Kohei Fujiwara

List of Publications by Year
in descending order

64 papers	1,228 citations	430874 18 h-index	395702 33 g-index
64 all docs	64 docs citations	64 times ranked	1928 citing authors

#	Article	IF	Citations
1	Improvement of the detectivity in an Feâ€“Sn magnetic-field sensor with a large current injection. Japanese Journal of Applied Physics, 2022, 61, SC1069.	1.5	1
2	<i>L</i>2₁ ordering of Co₂FeSn thin films promoted by high-temperature annealing. AIP Advances, 2022, 12, 065030.	1.3	0
3	Critical thickness for the emergence of Weyl features in Co3Sn2S2 thin films. Communications Materials, 2021, 2, .	6.9	23
4	Robust perpendicular magnetic anisotropy of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Co</mml:mi><mml:mn>3</mml:mn></mml: mathvariant="normal">S</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> phase in sulfur deficient sputtered thin films. Physical Review Materials, 2021, 5, .	2.4	7
5	First-principles investigation of magnetic and transport properties in hole-doped shandite compounds <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Co</mml:mi><mml:mn>3</mml:mn></mml: mathvariant="normal">S</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2021, 103, .	3.2	21
6	Two-dimensionality of metallic surface conduction in Co3Sn2S2 thin films. Communications Physics, 2021, 4, .	5.3	7
7	Electrostatic carrier doping of charge-ordered YbFe₂O₄ thin films using ionic liquids. Applied Physics Express, 2021, 14, 083001.	2.4	0
8	Three-dimensional sensing of the magnetic-field vector by a compact planar-type Hall device. Communications Materials, 2021, 2, .	6.9	8
9	Tuning scalar spin chirality in ultrathin films of the kagome-lattice ferromagnet Fe3Sn. Communications Materials, 2021, 2, .	6.9	4
10	Emergence of spin-orbit coupled ferromagnetic surface state derived from Zak phase in a nonmagnetic insulator FeSi. Science Advances, 2021, 7, eabj0498.	10.3	10
11	Formation of ilmenite-type single-crystalline MgTiO3 thin films by pulsed-laser deposition. AIP Advances, 2021, 11, .	1.3	4
12	Giant magneto-optical responses in magnetic Weyl semimetal Co3Sn2S2. Nature Communications, 2020, 11, 4619.	12.8	92
13	Stabilization of a honeycomb lattice of IrO6 octahedra by formation of ilmenite-type superlattices in MnTiO3. Communications Materials, 2020, 1, .	6.9	5
14	Signature of band inversion in the perovskite thin-film alloys <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>BaS</mml:mi><mml:msub><mml:mi mathvariant="normal">n</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â€“</mml:mo><mml:mi>x</mml:mi></mml:mrow>< mathvariant="normal">P</mml:mi><mml:msub><mml:mi mathvariant="normal">b</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>. Physi	3.2	10
15	Insulator-to-Metal Transition of Cr2O3 Thin Films via Isovalent Ru3+ Substitution. Chemistry of Materials, 2020, 32, 5272-5279.	6.7	5
16	Electrical detection of the antiferromagnetic transition in MnTiO3 ultrathin films by spin Hall magnetoresistance. Journal of Applied Physics, 2020, 127, 103903.	2.5	8
17	Magnetic-field-induced topological phase transition in Fe-doped <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mrow><mml:mo>(</mml:mo><mml:mrow><m mathvariant="normal">S</mml:mi><mml:msub><mml:mi mathvariant="normal">e</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> heterostructures. Physical Review Materials, 2020, 4, .	2.4	15
18	Anomalous Hall effect at the spontaneously electron-doped polar surface of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>PdCo</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> ultrathin films. Physical Review Research, 2020, 2, .	3.6	20

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19	Low-frequency noise measurements on Feâ€“Sn Hall sensors. Applied Physics Express, 2019, 12, 123001.	2.4	7
20	Ferromagnetic Co₃Sn₂S₂ thin films fabricated by co-sputtering. Japanese Journal of Applied Physics, 2019, 58, 050912.	1.5	26
21	Fe-Sn nanocrystalline films for flexible magnetic sensors with high thermal stability. Scientific Reports, 2019, 9, 3282.	3.3	26
22	Growth control of corundum-derivative MnSnO3 thin films by pulsed-laser deposition. AIP Advances, 2019, 9, 035210.	1.3	4
23	Thin-film stabilization of LiNbO3-type ZnSnO3 and MgSnO3 by molecular-beam epitaxy. APL Materials, 2019, 7, .	5.1	20
24	Formation of distorted rutile-type NbO2, MoO2, and WO2 films by reactive sputtering. Journal of Applied Physics, 2019, 125, .	2.5	14
25	Doping-induced enhancement of anomalous Hall coefficient in Fe-Sn nanocrystalline films for highly sensitive Hall sensors. APL Materials, 2019, 7, .	5.1	9
26	Improving resistance change with temperature and thermal stability in Fe₃O₄ films for high-temperature resistors. Applied Physics Express, 2019, 12, 011003.	2.4	3
27	Oxide Field-Effect Transistor with Polymer-Based Gate Insulator. IEEJ Transactions on Electronics, Information and Systems, 2019, 139, 207-210.	0.2	0
28	Fermi-level tuning of the Dirac surface state in (Bi_{1âˆ’<i>x</i>}Sb_{<i>x</i>})₂Se₃thin films. Journal of Physics Condensed Matter, 2018, 30, 085501.	1.8	13
29	Pulsed-laser deposition of InSe thin films for the detection of thickness-dependent bandgap modification. Applied Physics Letters, 2018, 113, .	3.3	9
30	Effect of the depletion region in topological insulator heterostructures for ambipolar field-effect transistors. Physical Review B, 2018, 98, .	3.2	7
31	High-mobility field-effect transistor based on crystalline ZnSnO3 thin films. AIP Advances, 2018, 8, .	1.3	6
32	Highly conductive PdCoO2 ultrathin films for transparent electrodes. APL Materials, 2018, 6, .	5.1	45
33	Enhancement of superconducting transition temperature in FeSe electric-double-layer transistor with multivalent ionic liquids. Physical Review Materials, 2018, 2, .	2.4	13
34	Enhanced electron mobility at the two-dimensional metallic surface of BaSnO3 electric-double-layer transistor at low temperatures. Applied Physics Letters, 2017, 110, .	3.3	26
35	Fabrication of tetragonal FeSeâ€“FeS alloy films with high sulfur contents by alternate deposition. Japanese Journal of Applied Physics, 2017, 56, 100308.	1.5	11
36	High field-effect mobility at the (Sr,Ba)SnO3/BaSnO3 interface. AIP Advances, 2016, 6, 085014.	1.3	16

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37	Impact of parylene-C thickness on performance of KTaO3 field-effect transistors with high-<i>k</i> oxide/parylene-C hybrid gate dielectric. Journal of Applied Physics, 2016, 119, .	2.5	5
38	Electric field-induced transport modulation in VO₂ FETs with high-<i>k</i> oxide/organic parylene-C hybrid gate dielectric. Applied Physics Letters, 2016, 108, 053503.	3.3	15
39	3D-Architected and Integrated Metal Oxide Nanostructures and Beyond Produced by Three-Dimensional Nanotemplate Pulsed Laser Deposition. E-Journal of Surface Science and Nanotechnology, 2015, 13, 279-283.	0.4	10
40	Identification of Giant Mott Phase Transition of Single Electric Nanodomain in Manganite Nanowall Wire. Nano Letters, 2015, 15, 4322-4328.	9.1	19
41	Discrimination between gate-induced electrostatic and electrochemical characteristics in insulator-to-metal transition of manganite thin films. Applied Physics Express, 2015, 8, 073201.	2.4	6
42	Estimation of dc transport dynamics in strongly correlated (La,Pr,Ca)MnO3 film using an insulator-metal composite model for terahertz conductivity. Applied Physics Letters, 2014, 105, .	3.3	6
43	Nonvolatile Transport States in Ferrite Thin Films Induced by Fieldâ€Effect Involving Redox Processes. Advanced Materials Interfaces, 2014, 1, 1300108.	3.7	14
44	Artificial three dimensional oxide nanostructures for high performance correlated oxide nanoelectronics. Japanese Journal of Applied Physics, 2014, 53, 05FA10.	1.5	6
45	Fabrication of three-dimensional epitaxial (Fe,Zn)₃O₄nanowall wire structures and their transport properties. Applied Physics Express, 2014, 7, 045201.	2.4	14
46	Electrical switching to probe complex phases in a frustrated manganite. Solid State Communications, 2014, 187, 64-67.	1.9	1
47	Dual field effects in electrolyte-gated spinel ferrite: electrostatic carrier doping and redox reactions. Scientific Reports, 2014, 4, 5818.	3.3	18
48	5d iridium oxide as a material for spin-current detection. Nature Communications, 2013, 4, 2893.	12.8	104
49	Electric-field breakdown of the insulating charge-ordered state in LuFe₂O₄thin films. Journal Physics D: Applied Physics, 2013, 46, 155108.	2.8	14
50	Nanowall-Shaped MgO Substrate with Flat (100) Sidesurface: A New Route to Three-Dimensional Functional Oxide Nanostructured Electronics. Japanese Journal of Applied Physics, 2013, 52, 015001.	1.5	20
51	Unstrained Epitaxial Zn-Substituted Fe3O4Films for Ferromagnetic Field-Effect Transistors. Japanese Journal of Applied Physics, 2013, 52, 068002.	1.5	6
52	In-Plane Oblique Pulsed-Laser Deposition and Its Application to the Fabrication of Metal Oxide Nanoconstrictions. Applied Physics Express, 2013, 6, 035201.	2.4	5
53	Observation of rebirth of metallic paths during resistance switching of metal nanowire. Applied Physics Letters, 2013, 103, 193114.	3.3	13
54	Controlled fabrication of artificial ferromagnetic (Fe,Mn)₃O₄nanowall-wires by a three-dimensional nanotemplate pulsed laser deposition method. Nanotechnology, 2012, 23, 485308.	2.6	16

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55	Tuning metal-insulator transition by one dimensional alignment of giant electronic domains in artificially size-controlled epitaxial VO2 wires. Applied Physics Letters, 2012, 101, 263111.	3.3	20
56	Three dimensional nano-seeding assembly of ferromagnetic Fe/LaSrFeO4 nano-hetero dot array. Journal of Applied Physics, 2012, 112, 024320.	2.5	12
57	V-V dimerization effects on bulk-sensitive hard x-ray photoemission spectra for MagnÃ©li phase vanadium oxides. Physical Review B, 2010, 81, .	3.2	13
58	Spatial Redistribution of Oxygen Ions in Oxide Resistance Switching Device after Forming Process. Japanese Journal of Applied Physics, 2010, 49, 060215.	1.5	15
59	Anomalous State Sandwiched between Fermi Liquid and Charge Ordered Mott-Insulating Phases of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>Ti</mml:mi><mml:mn>4</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="bold">O</mml:mi><mml:mn>7</mml:mn></mml:msub></mml:math>. Physical Review Letters, 2010, 104, 106401.	7.8	29
60	Inhomogeneous chemical states in resistance-switching devices with a planar-type Pt/CuO/Pt structure. Applied Physics Letters, 2009, 95, .	3.3	94
61	Electrode-Geometry Control of the Formation of a Conductive Bridge in Oxide Resistance Switching Devices. Applied Physics Express, 2009, 2, 081401.	2.4	7
62	Resistance Switching and Formation of a Conductive Bridge in Metal/Binary Oxide/Metal Structure for Memory Devices. Japanese Journal of Applied Physics, 2008, 47, 6266.	1.5	146
63	Accumulation and Depletion Layer Thicknesses in Organic Field Effect Transistors. Japanese Journal of Applied Physics, 2003, 42, L1408-L1410.	1.5	105
64	A large unidirectional magnetoresistance in Fe-Sn heterostructure devices. Japanese Journal of Applied Physics, 0, , .	1.5	0